

1. Record Nr.	UNINA9910783641103321
Autore	Baliga B. Jayant <1948->
Titolo	Silicon RF power MOSFETS [[electronic resource] /] / B. Jayant Baliga
Pubbl/distr/stampa	Singapore ; ; Hackensack, NJ, : World Scientific, c2005
ISBN	1-281-88100-7 9786611881009 981-256-932-4
Descrizione fisica	1 online resource (320 p.)
Disciplina	621.3815/284
Soggetti	Metal oxide semiconductor field-effect transistors Field-effect transistors
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references and index.
Nota di contenuto	Preface; Contents; Chapter 1 Introduction; Chapter 2 RF Power Amplifiers; Chapter 3 MOSFET PHYSICS; Chapter 4 Lateral-Diffused MOSFETs; Chapter 5 Vertical-Diffused MOSFETs; Chapter 6 Charge-Coupled MOSFETs; Chapter 7 Super-Linear MOSFETs; Chapter 8 Planar Super-Linear MOSFETs; Chapter 9 Dual Trench MOSFETs; Chapter 10 Hot Carrier Injection Instability; Chapter 11 Synopsis; Appendix; Index
Sommario/riassunto	The world-wide proliferation of cellular networks has revolutionizedtelecommunication systems. The transition from Analog to Digital RFtechnology enabled substantial increase in voice traffic usingavailable spectrum, and subsequently the delivery of digitally basedtext messaging, graphics and even streaming video.